

SSC8021GS6

P-Channel Enhancement Mode MOSFET with ESD Protection

> Features

VDS	VGS	RDSON Typ.	ID	ESD
-20V	±8V	0.45Ω@-4V5	0.74	2kV
		0.65Ω@-2V5	-0.7A	ZKV

> Description

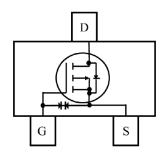
This device is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. The product does not contain Rohs substances such as lead and halogen.

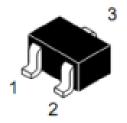
Applications

- Load Switch
- Portable Devices
- DCDC conversion

Pin configuration

Top view





SOT-23



Marking

Ordering Information

Device	Package	Shipping
SSC8021GS6	SOT-23	3000/Reel



➤ **Absolute Maximum Ratings**(T_A=25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	-20	V
V_{GSS}	Gate-to-Source Voltage	±12	V
I _D	Continuous Drain Current ^a	-0.7	Α
I _{DM}	Pulsed Drain Current ^b	-2.8	Α
P _D	Power Dissipation ^c	0.36	W
P _{DSM}	Power Dissipation ^a	0.29	W
TJ	Operation junction temperature	-55 to 150	°C
T _{STG}	Storage temperature range	-55 to 150	°C

➤ Thermal Resistance Ratings(T_A=25°C unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
R _{0JA}	Junction-to-Ambient Thermal Resistance		417	°C/W
Rejc	Junction-to-Case Thermal Resistance		346	C/ VV

Note:

- a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with T_A =25°C. The value in any given application depends on the user is specific board design. The current rating is based on the t \leq 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P_D is based on $T_{J(MAX)}$ =150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

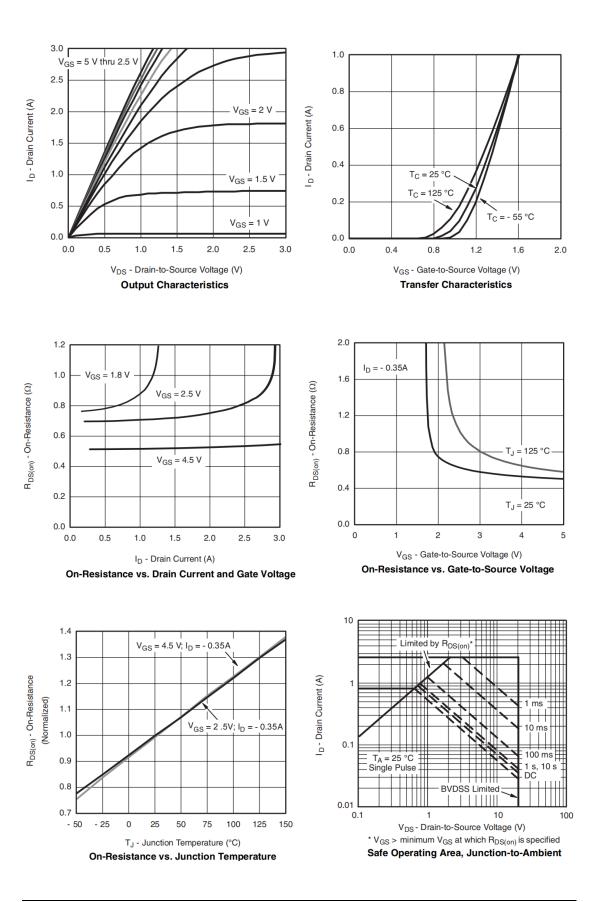


➤ **Electronics Characteristics**(T_A=25 °C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V,ID=-250uA	-20			٧
V _{GS (th)}	Gate Threshold Voltage	VDS=VGS,ID=-250uA	-0.4	-0.7	-1.0	V
_	Drain-Source On-	VGS=-4.5V,ID=-0.5A		450	560	0
R _{DS(on)}	Resistance	VGS=-2.5V,ID=-0.5A		650	780	mΩ
I _{DSS}	Zero Gate Voltage Drain Current	VDS=-16V,VGS=0V			-1	uA
I _{GSS}	Gate-Source leak	VGS=±12V,VDS=0V			±10	uA
G _{FS}	Transconductance	VDS=-5V,ID=-0.45A		1.5		S
V _{SD}	Forward Voltage	VGS=0V,IS=-0.15A			-1.1	V
Ciss	Input Capacitance	VDS=10V, VGS=0V, F=200KHZ		110		
Coss	Output Capacitance			25		pF
Crss	Reverse Transfer Capacitance			18		
T _{D(ON)}	Turn-on delay time	VGS=6V, VGEN=4.5V, RL=6Ω, RG=6Ω,ID=0.5A		55		
Tr	Rise time			84		nc
T _{D(OFF)}	Turn-off delay time			880		ns
Tf	Fall time			175		

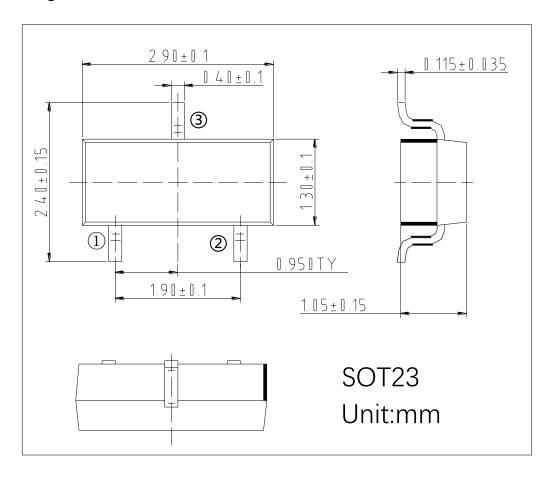


➤ Typical Characteristics(T_A=25°C unless otherwise noted)





Package Information





DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.